

EAST - 109942580.wsu.1

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L1: (19) US-6101131-S.DID. OR US-6127227-S.DID. OR US-616

L5: (0) L1 and (flash nonvolatile (non adj volatile)) and

L6: (3) L1 and (flash nonvolatile (non adj volatile)) and

(9) ((pillar with substrate) and (controlS4 adj2 gate) an

(96) (pillar with substrate) and (controlS4 near3 gate) a

(264S) pillar with substrate

(85) (pillar with substrate) and (controlS4 adj2 gate) an

(20) ((pillar with substrate) and (controlS4 near3 gate)

(9) ((pillar with substrate) and (controlS4 near3 gate) a

(15) (pillar with substrate) and (programS5 near2 decodS3

(41) (pillar with substrate) and (programS5 with decodS3)

(24) low adj2 tunnel adj2 barrier

(537) programmable adj2 decoder

(424) (programmable adj2 decoder) and memory

(17) ((programmable adj2 decoder) and memory) and (vertic

(4) 6210999.pn. 6541280.pn.

DB: USPA1

Default operator: GR

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L1 and (Flash nonvolatile (non adj volatile)) and (vertical adj2 (channel gate pillar))

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| 1 | <input type="checkbox"/>            | <input type="checkbox"/> | US 6475857 B1 | 20021105   | 20    | Method of making a scalable two transistor memory device | 438/240    | 438/258              |             | Kim, Woosik et al.       | <input checked="" type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> |
| 2 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 5617351 A  | 19970401   | 19    | Three-dimensional direct-write EEPROM arrays             | 365/185.05 | 257/298;<br>257/302; |             | Bertin, Claude L. et al. | <input type="checkbox"/>            | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> |
| 3 | <input checked="" type="checkbox"/> | <input type="checkbox"/> | US 5455792 A  | 19951003   | 21    | Flash EEPROM devices employing mid channel               | 365/185.15 | 257/316;<br>257/319; |             | Yi, Yong-Wan             | <input type="checkbox"/>            | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> | <input type="checkbox"/> |

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| 1           | 537  | programmable adj2 decoder   | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/12/11<br>13:56 |
| 2           | 424  | (programmable adj2 decoder) and memory  | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/12/11<br>13:56 |
| 3           | 17   | ((programmable adj2 decoder) and memory)<br>and (vertical adj3 (pillar gate channel)) | USPAT;<br>US-PGPUB;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | 2003/12/11<br>13:57 |